/ Descriptions

TR0555 QSQ Silicon NPN transistor in a TO-252 Plastic Package.

/ Features

$V_{FH+vaw,}$ /h_{IH}

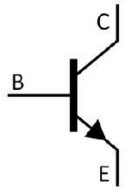
Low saturation voltage,excellent h_{FE} linearity and high h_{FE}.

/ Applications

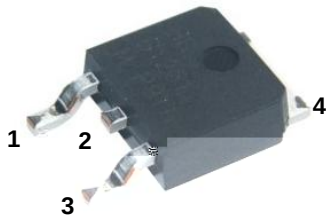
6 ב / /

Output stage of 3 watts audio amplifier, voltage regulator, DC-DC converter and relay driver.

/ Equivalent Circuit



/ Pinning



PIN1 Base PIN 2,4 Collector PIN 3 Emitter

/ h_{FE} Classifications & Marking

h_{FE} Classifications Symbol	R	Q	P	E
h_{FE} Range	60 120	100 200	160 320	200 400

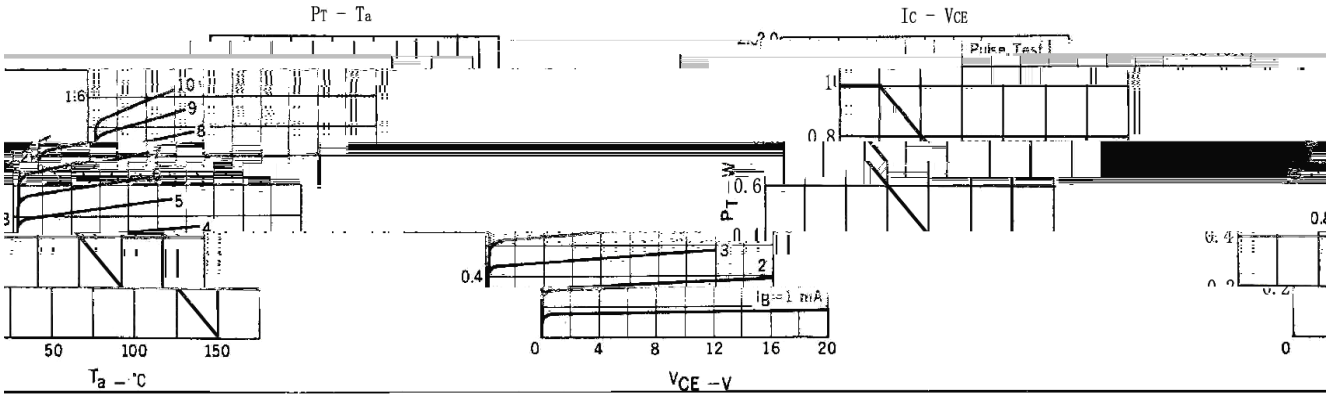
/ Absolute Maximum Ratings(Ta=25)

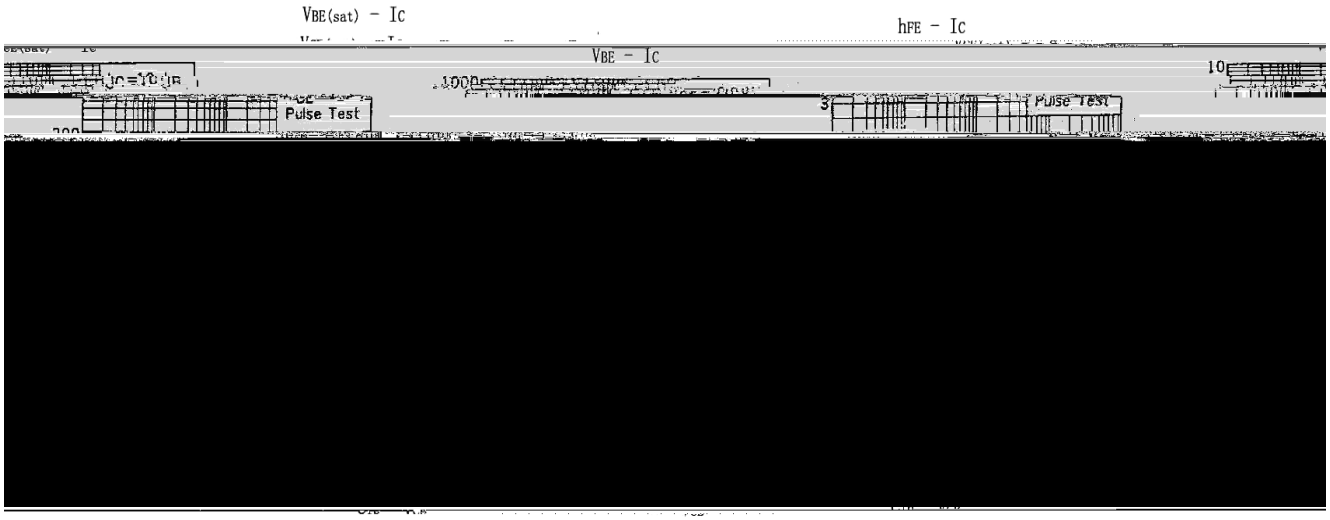
Parameter	N Symbol	Rating	Unit
Collector to Base Voltage	V_{CBO}	40	V
Collector to Emitter Voltage	V_{CEO}	30	V
Emitter to Base Voltage	V_{EBO}	5.0	V
Collector Current - Continuous	I_C	3.0	A
Collector Power Dissipation	P_C	1.0	W
	$P_{C(Tc=25\ )}$	10	W
Junction Temperature	T_j	150	
Storage Temperature Range	T_{stg}	-55 150	

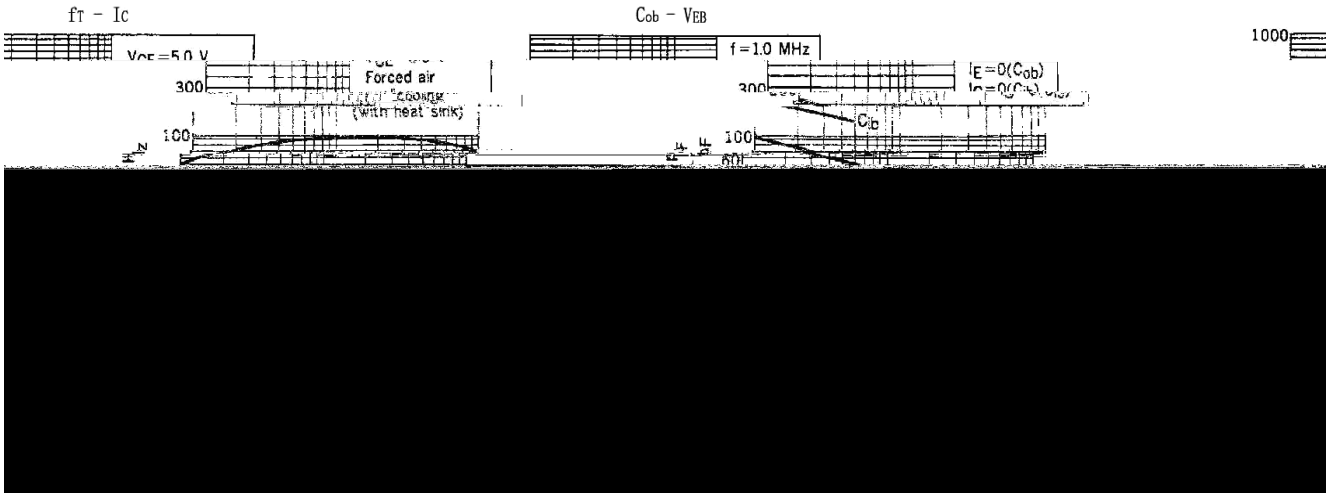
/ Electrical Characteristics(Ta=25)

Parameter	N Symbol	Test Conditions	Min	Typ	Max	Unit
Collector Cut-Of I	CBO	V_{CB}=30V I_E=0			1.0	μA
	EBO	EB C				
DC Current Gain	$h_{FE(1)}$	V_{CE}=2.0V I_C=1.0A	60	160	400	
	$h_{FE(2)}$	V_{CE}=2.0V I_C=20mA	30	150		
Collector to Emitter Saturation Voltage	$V_{CE(sat)}$	I_C=2.0A I_B=0.2A		0.3	0.5	V
Base to Emitter Saturation Voltage	$V_{BE(sat)}$	I_C=2.0A I_B=0.2A		1.0	2.0	V
Transition Frequency	f_T	V_{CE}=5.0V I_C=0.1A		90		MHz
Collector output capacitance	C_{ob}	V_{CB}=10V I_E=0 f=1.0MHz		45		pF

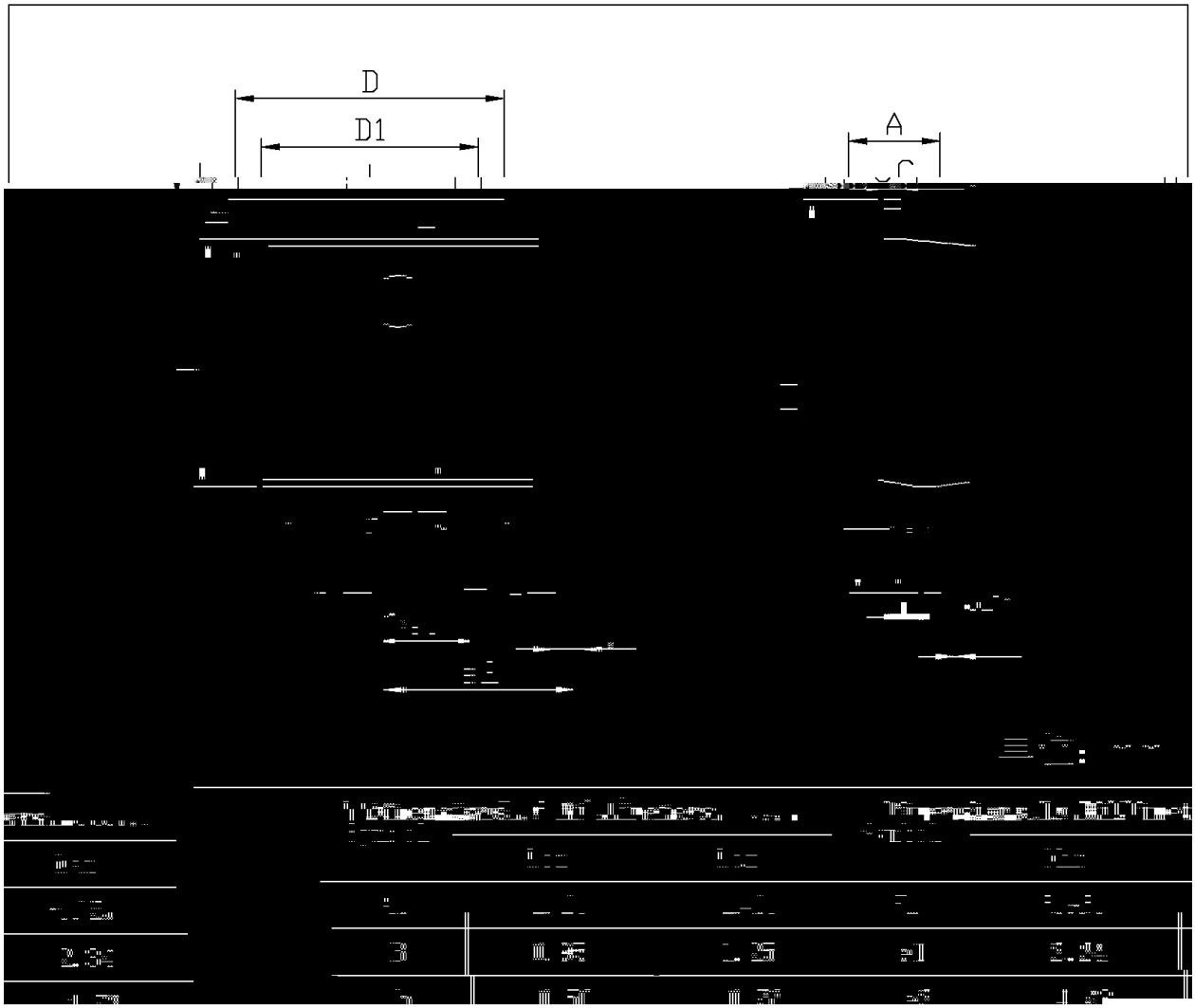
/ Electrical Characteristic Curve



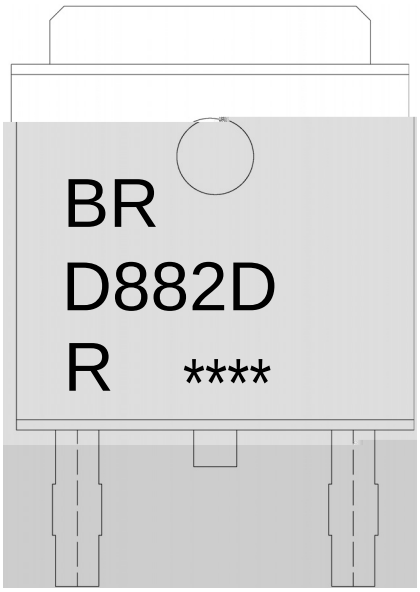




/ Package Dimensions



/ Marking Instructions

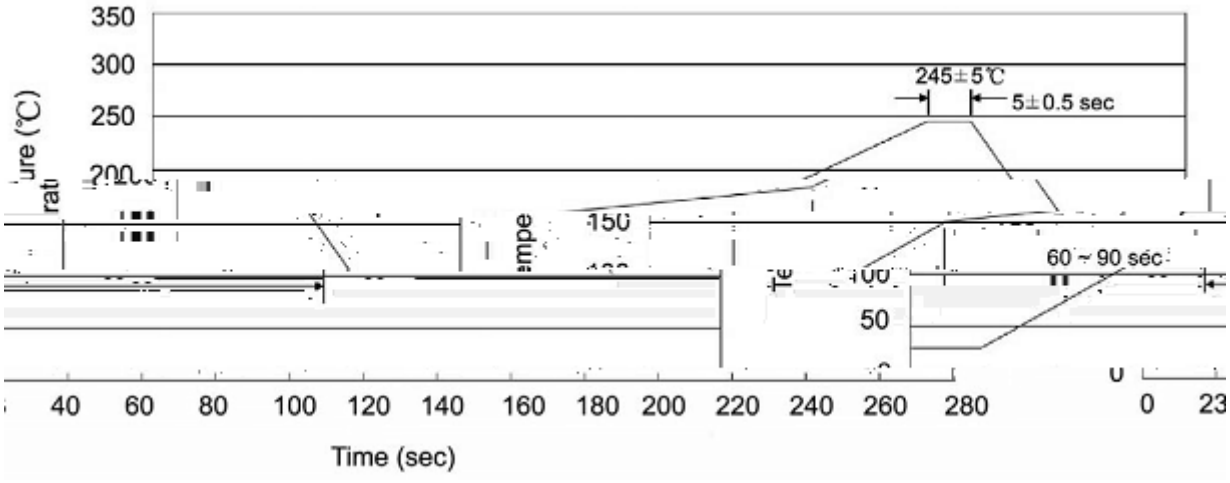


ER	И
G885G	N
R:	h_{IH}
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Note:

BR:	Company Code
D882D:	Product Type.
R:	h_{FE} Classifications Symbol
****:	Lot No. Code, code change with Lot No.

( ) / Temperature Profile for IR Reflow Soldering(Pb-Free)



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